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April 2016

FODM8801A, FODM8801B, FODM8801C OptoHiT™ Series, High-Temperature Phototransistor Optocoupler in Half-Pitch Mini-Flat 4-Pin Package

Features

- Utilizing Proprietary Process Technology to Achieve High Operating Temperature: up to 125°C
- Guaranteed Current Transfer Ratio (CTR)
 Specifications Across Full Temperature Range
 - Excellent CTR Linearity at High-Temperature
 - CTR at Very Low Input Current, IF
- High Isolation Voltage Regulated by Safety Agency: C-UL / UL1577, 3750 VAC_{RMS} for 1 minute and DIN EN/IEC60747-5-5
- Compact Half-Pitch, Mini-Flat, 4-Pin Package (1.27 mm Lead Pitch, 2.4 mm Maximum Standoff Height)
- > 5 mm Creepage and Clearance Distance
- Applicable to Infrared Ray Reflow, 245°C

Applications

- · Primarily Suited for DC-DC Converters
- Ground-Loop Isolation, Signal-Noise Isolation
- Communications Adapters, Chargers
- Consumer Appliances, Set-Top Boxes
- Industrial Power Supplies, Motor Control, Programmable Logic Control

Description

In the OptoHiT™ series, the FODM8801 is a first-of-kind phototransistor, utilizing Fairchild's leading-edge proprietary process technology to achieve high operating temperature characteristics, up to 125°C. The opto-coupler consists of an aluminum gallium arsenide (AlGaAs) infrared light-emitting diode (LED) optically coupled to a phototransistor, available in a compact half-pitch, mini-flat, 4-pin package. It delivers high current transfer ratio at very low input current. The input-output isolation voltage, V_{ISO}, is rated at 3750 VAC_{RMS}.

Schematic Package

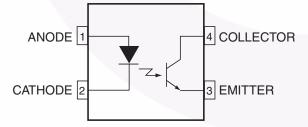


Figure 1. Schematic

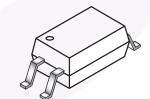


Figure 2. Half-Pitch Mini-Flat

Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter	Characteristics	
Installation Classifications per DIN VDE	< 150 V _{RMS}	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V _{RMS}	I–III
Climatic Classification	45/125/21	
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	848	V _{peak}
V _{PR}	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1$ s, Partial Discharge < 5 pC	1060	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	565	V_{peak}
V_{IOTM}	Highest Allowable Over-Voltage	6000	V_{peak}
	External Creepage	≥ 5	mm
	External Clearance	≥ 5	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.5	mm
T _S	Case Temperature ⁽¹⁾	150	°C
I _{S,INPUT}	Input Current ⁽¹⁾	200	mA
P _{S,OUTPUT}	Output Power ⁽¹⁾	300	mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V ⁽¹⁾	> 10 ⁹	Ω

Note:

1. Safety limit values – maximum values allowed in the event of a failure.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A = 25$ °C unless otherwise specified.

Symbol	Parameter	Value	Unit
Total Package			
T _{STG}	Storage Temperature	-40 to +150	°C
T _{OPR}	Operating Temperature	-40 to +125	°C
T _J	Junction Temperature	-40 to +140	°C
T _{SOL}	Lead Solder Temperature	245 for 10 s	°C
Emitter			
I _{F(average)}	Continuous Forward Current	20	mA
V _R	Reverse Input Voltage	6	V
PD _{LED}	Power Dissipation ⁽²⁾⁽⁴⁾	40	mW
Detector			
I _{C(average)}	Continuous Collector Current	30	mA
V _{CEO}	Collector-Emitter Voltage	75	V
V _{ECO}	Emitter-Collector Voltage	7	V
$PD_{\mathbb{C}}$	Collector Power Dissipation ⁽³⁾⁽⁴⁾	150	mW

Notes:

- 2. Derate linearly from 73°C at a rate of 0.24 mW/°C
- 3. Derate linearly from 73°C at a rate of 2.23 mW/°C.
- 4. Functional operation under these conditions is not implied. Permanent damage may occur if the device is subjected to conditions outside these ratings.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Value	Unit
T _A	Operating Temperature	-40 to +125	°C
V _{FL(OFF)}	Input Low Voltage	-5.0 to +0.8	V
I _{FH}	Input High Forward Current	1 to 10	mA

Isolation Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V _{ISO}	Input-Output Isolation Voltage	$f = 60 \text{ Hz}, t = 1 \text{ min.}, I_{I-O} \le 10 \mu A^{(5)(6)}$	3,750			VAC _{RMS}
R _{ISO}	Isolation Resistance	$V_{I-O} = 500 V^{(5)}$	10 ¹²			Ω
C _{ISO}	Isolation Capacitance	f = 1 MHz		0.3	0.5	pF

Notes:

5. Device is considered a two-terminal device: pins 1 and 2 are shorted together and pins 3 and 4 are shorted together. 6.3,750 VAC_{RMS} for 1 minute is equivalent to 4,500 VAC_{RMS} for 1 second.

Electrical Characteristics

Apply over all recommended conditions (T_A = -40°C to +125°C unless otherwise specified). All typical values are measured at T_A = 25°C.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Emitter		1			l	
V _F	Forward Voltage	I _F = 1 mA	1.00	1.35	1.80	V
$\Delta V_F / \Delta T_A$	Forward-Voltage Coefficient	I _F = 1 mA		-1.6		mV / °C
I _R	Reverse Current	V _R = 6 V			10	μA
C _T	Terminal Capacitance	V = 0 V, f = 1 MHz		30		pF
Detector						
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 0.5 \text{ mA}, I_F = 0 \text{ mA}$	75	130		V
BV _{ECO}	Emitter-Collector Breakdown Voltage	I _E = 100 μA, I _F = 0 mA	7	12		V
		$V_{CE} = 75 \text{ V, } I_F = 0 \text{ mA,}$ $T_A = 25^{\circ}\text{C}$			100	nA
I _{CEO}	Collector Dark Current	$V_{CE} = 50 \text{ V}, I_F = 0 \text{ mA}$			50	μA
		$V_{CE} = 5 \text{ V}, I_F = 0 \text{ mA}$			30	μA
C _{CE}	Capacitance	$V_{CE} = 0 \text{ V, } f = 1 \text{ MHz}$		8		pF

Transfer Characteristics

Apply over all recommended conditions (T_A = -40°C to +125°C unless otherwise specified). All typical values are measured at T_A = 25°C.

Symbol	Parameter	Device	Conditions	Min.	Тур.	Max.	Unit
			$I_F = 1.0 \text{ mA}, V_{CE} = 5 \text{ V}$ @ $T_A = 25^{\circ}\text{C}$	80	120	160	
		FODM8801A	$I_F = 1.0 \text{ mA}, V_{CE} = 5 \text{ V}$	35	120	230	
			$I_F = 1.6 \text{ mA}, V_{CE} = 5 \text{ V}$	40	125		
			$I_F = 3.0 \text{ mA}, V_{CE} = 5 \text{ V}$	45	138		
	0		I _F = 1.0 mA, V _{CE} = 5 V @ T _A = 25°C	130	195	260	
CTR _{CE}	Current Transfer Ratio	FODM8801B	I _F = 1.0 mA, V _{CE} = 5 V	65	195	360	%
0_	(Collector-Emitter)		$I_F = 1.6 \text{ mA}, V_{CE} = 5 \text{ V}$	70	202		
			$I_F = 3.0 \text{ mA}, V_{CE} = 5 \text{ V}$	75	215		
			I _F = 1.0 mA, V _{CE} = 5 V @ T _A = 25°C	200	300	400	
		FODM8801C	$I_F = 1.0 \text{ mA}, V_{CE} = 5 \text{ V}$	100	300	560	
			$I_F = 1.6 \text{ mA}, V_{CE} = 5 \text{ V}$	110	312		
			$I_F = 3.0 \text{ mA}, V_{CE} = 5 \text{ V}$	115	330		
			$I_F = 1.0 \text{ mA}, V_{CE} = 0.4 \text{ V}$ @ $T_A = 25^{\circ}\text{C}$	65	108	150	
		FODM8801A	$I_F = 1.0 \text{ mA}, V_{CE} = 0.4 \text{ V}$	30	108		
			$I_F = 1.6 \text{ mA}, V_{CE} = 0.4 \text{ V}$	25	104		
			$I_F = 3.0 \text{ mA}, V_{CE} = 0.4 \text{ V}$	20	92		
	Saturated Current		I _F = 1.0 mA, V _{CE} = 0.4 V @ T _A = 25°C	90	168	245	
CTR _{CE(SAT)}	Transfer Ratio	FODM8801B	$I_F = 1.0 \text{ mA}, V_{CE} = 0.4 \text{ V}$	45	168		%
J=(J)	(Collector-Emitter)		$I_F = 1.6 \text{ mA}, V_{CE} = 0.4 \text{ V}$	40	155		
			$I_F = 3.0 \text{ mA}, V_{CE} = 0.4 \text{ V}$	35	132		
			$I_F = 1.0 \text{ mA}, V_{CE} = 0.4 \text{ V}$ @ $T_A = 25^{\circ}\text{C}$	140	238	380	
		FODM8801C	$I_F = 1.0 \text{ mA}, V_{CE} = 0.4 \text{ V}$	75	238	y	
			$I_F = 1.6 \text{ mA}, V_{CE} = 0.4 \text{ V}$	65	215		
			$I_F = 3.0 \text{ mA}, V_{CE} = 0.4 \text{ V}$	55	177		
			$I_F = 1.0 \text{ mA}, I_C = 0.3 \text{ mA}$		0.17	0.40	
	FODM880	FODM8801A	$I_F = 1.6 \text{ mA}, I_C = 0.4 \text{ mA}$		0.16	0.40	
V _{CE(SAT)}			$I_F = 3.0 \text{ mA}, I_C = 0.6 \text{ mA}$		0.15	0.40	
			I _F = 1.0 mA, I _C = 0.45 mA		0.17	0.40	
	Saturation Voltage	FODM8801B	I _F = 1.6 mA, I _C = 0.6 mA		0.16	0.40	V
			$I_F = 3.0 \text{ mA}, I_C = 1.0 \text{ mA}$		0.16	0.40	
			$I_F = 1.0 \text{ mA}, I_C = 0.75 \text{ mA}$		0.18	0.40	
		FODM8801C	I _F = 1.6 mA, I _C = 1.0 mA		0.17	0.40	
			$I_F = 3.0 \text{ mA}, I_C = 1.6 \text{ mA}$		0.17	0.40	

Switching Characteristics

Apply over all recommended conditions (T_A = -40°C to +125°C unless otherwise specified). All typical values are measured at T_A = 25°C.

Symbol	Parameter	Device	Conditions	Min.	Тур.	Max.	Unit
tou	Turn-On Time	All Devices	$I_F = 1.6 \text{ mA}, V_{CC} = 5 \text{ V},$ $R_L = 0.75 \text{ k}\Omega$	1	6	20	
t _{ON}	Turr-On nine	All Devices	$I_F = 1.6 \text{ mA}, V_{CC} = 5 \text{ V},$ $R_L = 4.7 \text{ k}\Omega$		6		μs
torr	Turn-Off Time	All Devices	$I_F = 1.6 \text{ mA}, V_{CC} = 5 \text{ V},$ $R_L = 0.75 \text{ k}\Omega$	1	6	20	μs
toff	Tulli-Oil Tillie	All Devices	$I_F = 1.6 \text{ mA}, V_{CC} = 5 \text{ V},$ $R_L = 4.7 \text{ k}\Omega$		40		μο
t _R	Output Rise Time (10% to 90%)	All Devices	$I_F = 1.6 \text{ mA}, V_{CC} = 5 \text{ V},$ $R_L = 0.75 \text{ k}\Omega$		5		μs
t _F	Output Fall Time (90% to 10%)	All Devices	$I_F = 1.6 \text{ mA}, V_{CC} = 5 \text{ V},$ $R_L = 0.75 \text{ k}\Omega$		5.5		μs
CM _H	Common-Mode Rejection Voltage (Transient Immunity) – Output High	All Devices	T_A = 25°C, I_F = 0 mA, V_O > 2.0 V, R_L = 4.7 kΩ, V_{CM} = 1000 $V^{(7)}$, Figure 16		20		kV / µs
CM _L	Common-Mode Rejection Voltage (Transient Immunity) – Output Low	All Devices	T_A = 25°C, I_F = 1.6 mA, V_O < 0.8 V, R_L = 4.7 kΩ, V_{CM} = 1000 V ⁽⁷⁾ , Figure 16		20		kV / µs

Note:

7. Common-mode transient immunity at output high is the maximum tolerable positive dVcm/dt on the leading edge of the common-mode impulse signal, V_{CM} , to assure that the output remains high.

Typical Performance Curves

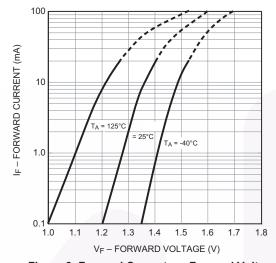


Figure 3. Forward Current vs. Forward Voltage

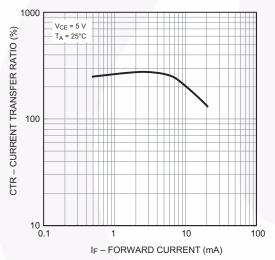


Figure 5. Current Transfer Ratio vs. Forward Current

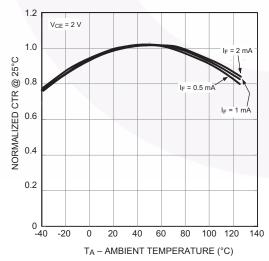


Figure 7. Normalized CTR vs. Ambient Temperature

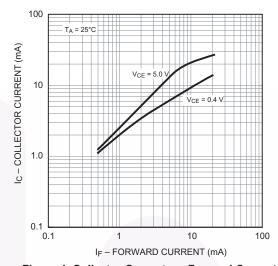


Figure 4. Collector Current vs. Forward Current

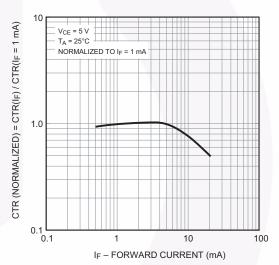


Figure 6. Normalized CTR vs. Forward Current

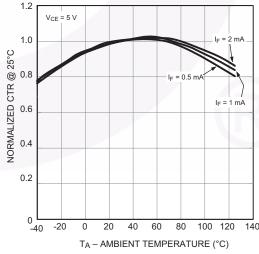


Figure 8. Normalized CTR vs. Ambient Temperature

Typical Performance Curves (Continued)

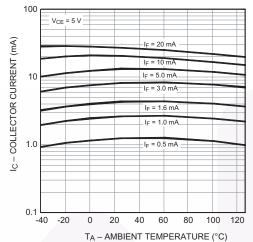


Figure 9. Collector Current vs.
Ambient Temperature

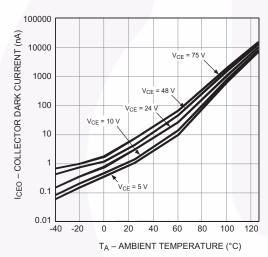


Figure 11. Collector Dark Current vs.
Ambient Temperature

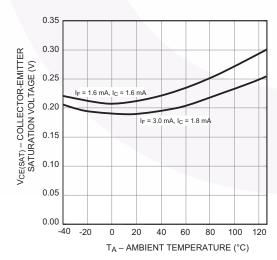


Figure 13. Collector-Emitter Saturation Voltage vs. Ambient Temperature

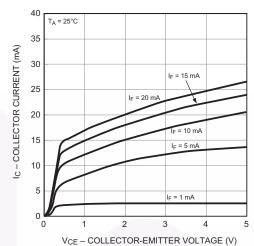


Figure 10 Collector Current vs.
Collector-Emitter Voltage

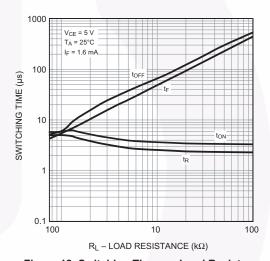


Figure 12. Switching Time vs. Load Resistance

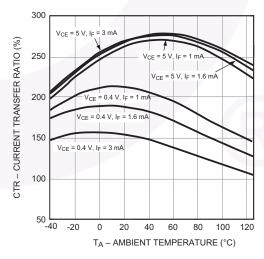


Figure 14. Current Transfer Ration vs. Ambient Temperature

Test Circuits

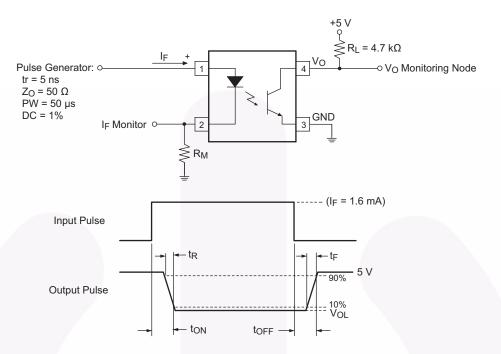


Figure 15. Test Circuit for Propagation Delay, Rise Time, and Fall Time

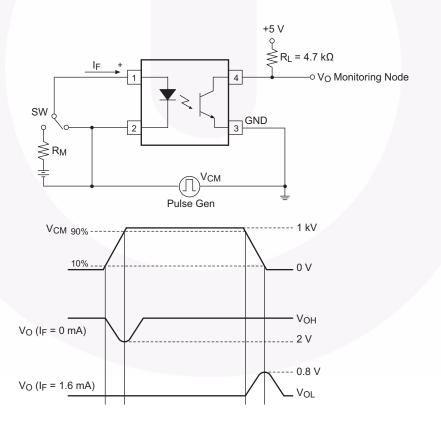
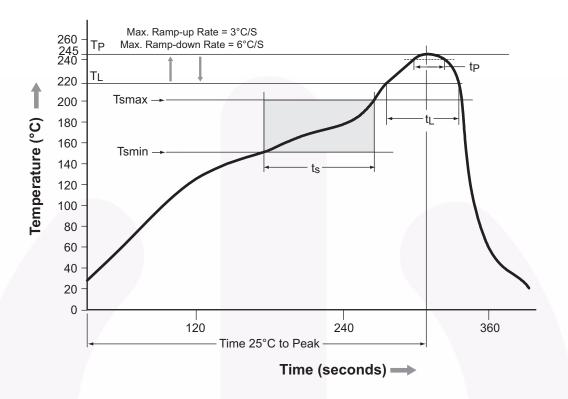


Figure 16. Test Circuit for Instantaneous Common-Mode Rejection Voltage

Reflow Profile



Profile Freature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (t _S) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60-150 seconds
Peak Body Package Temperature	245°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

Figure 17. Reflow Profile

Ordering Information

Part Number	Package	Packing Method
FODM8801A	Half Pitch Mini-Flat 4-Pin	Tube (100 units)
FODM8801AR2	Half Pitch Mini-Flat 4-Pin	Tape and Reel (2500 Units)
FODM8801AV	Half Pitch Mini-Flat 4-Pin, DIN EN/IEC60747-5-5 Option	Tube (100 Units)
FODM8801AR2V	Half Pitch Mini-Flat 4-Pin, DIN EN/IEC60747-5-5 Option	Tape and Reel (2500 Units)

Note:

8. The product orderable part number system listed in this table also applies to the FODM8801B, FODM8801C products.

Marking Information

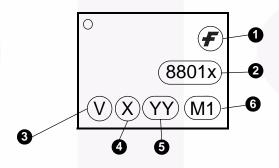
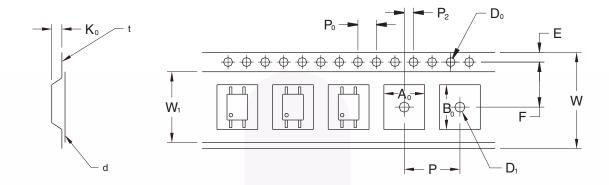


Figure 18. Top Mark

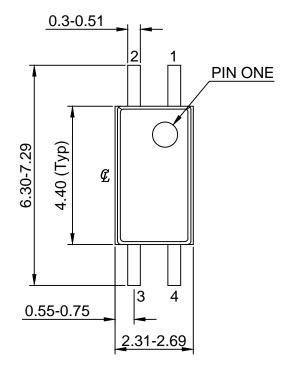
Table 1. Top Mark Definitions

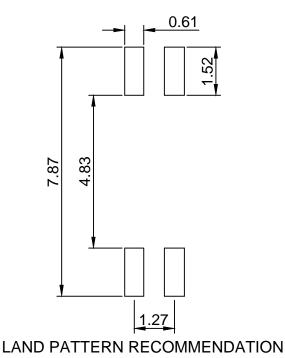
1	Fairchild Logo
2	Device Number
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
4	One-Digit Year Code, e.g., "6"
5	Digit Work Week, Ranging from "01" to "53"
6	Assembly Package Code

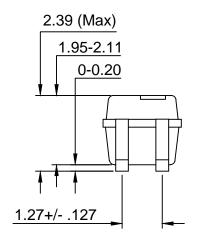
Tape and Reel Dimensions

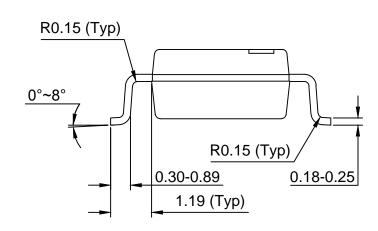


		1.27 Pitch
Description	Symbol	Dimensions (mm)
Tape Width	W	12.00 +0.30/-0.10
Tape Thickness	t	0.30 ±0.05
Sprocket Hole Pitch	P ₀	4.00 ±0.10
Sprocket Hole Diameter	D ₀	1.50 +0.10/-0.0
Sprocket Hole Location	E	1.75 ±0.10
Pocket Location	F	5.50 ±0.10
	P ₂	2.00 ±0.10
Pocket Pitch	Р	8.00 ±0.10
Pocket Dimension	A ₀	2.80 ±0.10
	B ₀	7.30 ±0.10
	K ₀	2.30 ±0.10
Pocket Hole Diameter	D ₁	1.50 Min.
Cover Tape Width	W ₁	9.20
Cover Tape Thickness	d	0.065 ±0.010
Max. Component Rotation or Tilt		10° Max.
Devices Per Reel		2500
Reel Diameter		330 mm (13")









NOTES:

- A) NO STANDARD APPLIES TO THIS PACKAGE
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSION
- D) DRAWING FILENAME AND REVSION: MKT-MFP04AREV4.







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Definition of Terms

Definition of Terms		
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